

Title (en)  
MEMORY SELECTOR

Title (de)  
SPEICHERSELEKTOR

Title (fr)  
SELECTEUR DE MEMOIRE

Publication  
**EP 3966874 A1 20220316 (FR)**

Application  
**EP 20731925 A 20200504**

Priority  
• FR 1904900 A 20190510  
• FR 2020050741 W 20200504

Abstract (en)  
[origin: WO2020229752A1] The present description relates to a selector (33) for a memory cell (3), which selector is intended to switch from a resistive state to a conducting state so as to respectively prevent or allow access to the memory cell, characterized in that it consists of an alloy consisting of germanium, selenium, arsenic and tellurium.

IPC 8 full level  
**H01L 45/00** (2006.01)

CPC (source: EP US)  
**H10B 63/24** (2023.02 - EP US); **H10B 63/80** (2023.02 - EP); **H10N 70/026** (2023.02 - US); **H10N 70/20** (2023.02 - EP); **H10N 70/826** (2023.02 - EP); **H10N 70/882** (2023.02 - EP); **H10N 70/8825** (2023.02 - US); **H10N 70/8828** (2023.02 - US); **H10B 63/84** (2023.02 - US)

Citation (search report)  
See references of WO 2020229752A1

Designated contracting state (EPC)  
AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

Designated extension state (EPC)  
BA ME

DOCDB simple family (publication)  
**FR 3095894 A1 20201113**; **FR 3095894 B1 20220520**; CN 114072929 A 20220218; EP 3966874 A1 20220316; US 2022231225 A1 20220721; WO 2020229752 A1 20201119

DOCDB simple family (application)  
**FR 1904900 A 20190510**; CN 202080049852 A 20200504; EP 20731925 A 20200504; FR 2020050741 W 20200504; US 202017609862 A 20200504